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APPLIED PHYSICS

p-type transparent superconductivity in a layered oxide

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Development of p-type transparent conducting materials has been a challenging issue. The known p-type transparent conductors unsatisfy both of high transparency and high conductivity nor exhibit superconductivity. Here, we report on epitaxial synthesis, excellent p-type transparent conductivity, and two-dimensional superconductivity of $\text{Li}_{1-x}\text{NbO}_2$. The LiNbO_2 epitaxial films with NbO_2 sheets parallel to (111) plane of cubic MgAl_2O_4 substrates were stabilized by heating amorphous films. The hole doping associated with Li^+ ion deintercalation triggered superconductivity below 4.2 kelvin. Optical measurements revealed that the averaged transmittance to the visible light of ~ 100 -nanometer-thick $\text{Li}_{1-x}\text{NbO}_2$ was $\sim 77\%$, despite the large number of hole carriers exceeding 10^{22} per cubic centimeter. These results indicate that $\text{Li}_{1-x}\text{NbO}_2$ is a previously unknown p-type transparent superconductor, in which strongly correlated electrons at the largely isolated Nb $4d_{z^2}$ band play an important role for the high transparency.

INTRODUCTION

Search for new transparent conductors (TCs) is one of the most important subjects not only for practical use but also for advances in materials science (1). In case of n-type TCs, a variety of materials have been developed and used in industry. For example, Sn-doped In_2O_3 (ITO) exhibits high conductivity ($\sim 6000 \text{ S cm}^{-1}$) and high transparency ($\sim 80\%$) (2). Furthermore, even a transparent superconductor (TSC), which is regarded as an ultimate TC, was reported for LiTi_2O_4 epitaxial films (3). In contrast to n-type TCs, however, p-type TCs (p-TCs) are subjects of fundamental research since their performances are still low (4).

Zhang *et al.* (5) recently proposed new strategy for designing TCs based on transition-metal oxides (TMOs). In contrast to a traditional concept (taking ITO as an example, high-mobility semiconductor In_2O_3 is doped with a small amount of Sn), they shed light on correlated metals, where large number of carriers resides in low-mobility TMOs. On the basis of this strategy, perovskite-type AMO_3 ($A = \text{Ca, Sr, and La}$; $M = \text{V, Mo, and Cr}$) have been found to be good TCs, both n- and p-type (5–8). However, the studies have been so far limited to the perovskite-type TMOs. Thus, further investigation on other TMOs will pave a way for better p-TC performances.

To realize an excellent p-TC and p-type TSC (p-TSC), one may investigate two-dimensional materials, which have been enthusiastically studied in these days (9). Among various TMOs, we focus on a layered niobate, which is the only isostructural oxide to 2H-type transition-metal dichalcogenide (TMD) such as MoS_2 (10). The crystal structure of LiNbO_2 consists of NbO_6 triangular prisms (Fig. 1A), which are thought to create characteristic d-band splitting for realizing p-type conduction (11, 12). Similar to TMDs, exotic properties can be expected (13, 14). In addition, the wide bandgap nature of TMOs provides high transparency in the visible range (15). However, electronic properties of LiNbO_2 are still unclear. Although superconductivity was observed below 5 K in a Li-deficient phase $\text{Li}_{1-x}\text{NbO}_2$ ($x \sim 0.5$) (16), its electronic properties have not been investigated in detail (17). Moreover, there is no report about single-crystalline su-

perconducting films, and their transport and optical properties are not yet fully understood.

Here, we fabricated superconducting $\text{Li}_{1-x}\text{NbO}_2$ epitaxial films using three-step synthesis method as illustrated in Fig. 1B and investigated their electronic properties. p-type doping associated with Li^+ ion deintercalation to LiNbO_2 triggered superconductivity and enhanced transparency in the visible range, and we created a p-TSC with strongly correlated electrons in two-dimensional NbO_2 conduction layers and isolated Nb $4d_{z^2}$ band derived from the NbO_6 triangular prism coordination.

RESULTS

Three-step synthesis and structural properties

Figure 1C shows out-of-plane x-ray diffraction (XRD) profiles of Li-Nb-O films. The films prepared by the high-temperature direct growth (direct) showed 002 reflection of layered LiNbO_2 at $2\theta = 17.0^\circ$ and a number of reflections from secondary phases, Li_3NbO_4 222, NbO_2 440, and LiNbO_3 006 at $2\theta = 36.8^\circ$, 37.3° , and 38.9° , respectively (18, 19). The pulsed laser deposition (PLD) growth of Li-containing materials such as LiCoO_2 and LiTi_2O_4 often tends to form Li-deficient phases because Li atoms are easily scattered by gaseous species and/or reevaporated from the growing surface (20, 21). In our case, however, the Li-rich phase (Li_3NbO_4) indicated much stronger peak than the Li-deficient phase (NbO_2) and stoichiometric phases (LiNbO_2 and LiNbO_3). The inclusion and unusual stability of Li_3NbO_4 were further verified by its excellent crystallinity irrespective of growth conditions (see section S1).

To avoid the formation of the secondary phases and to create layered LiNbO_2 , we developed a three-step synthesis, which was initiated from PLD growth of Li-Nb-O films on the unheated substrates (step 1). Out-of-plane XRD profiles of the films at each step are also shown in Fig. 1C. In step 1, no film peak was observed, suggesting the amorphous phase. After in situ reductive annealing (step 2), clear 00 l reflections of LiNbO_2 phase appeared without Li_3NbO_4 peaks despite the condition identical to the direct growth. A small peak of the oxidized phase (LiNbO_3) is thought to originate from partial oxidation of the LiNbO_2 phase. LiNbO_3 has wide bandgap and insulating nature and does not affect the transport and optical properties described below. Last, the LiNbO_2 films were immersed into an $\text{I}_2/\text{CH}_3\text{CN}$ solution to deintercalate Li^+ ions

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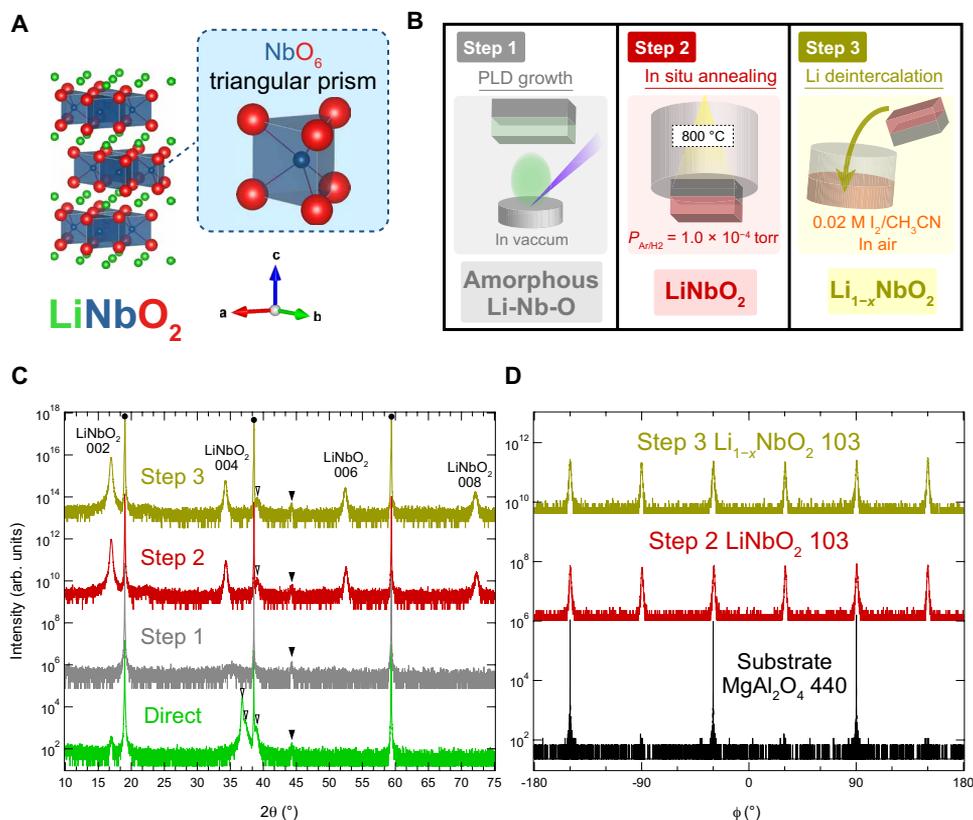
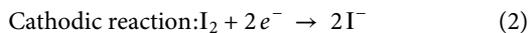
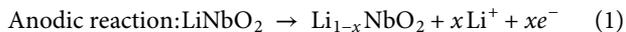


Fig. 1. Three-step synthesis method and structural analysis for $\text{Li}_{1-x}\text{NbO}_2$ epitaxial films. (A) Schematic crystal structure of LiNbO_2 . The green, blue, and red spheres indicate lithium, niobium, and oxygen atoms, respectively. The magnified unit of NbO_6 takes a triangular prism structure. (B) Schematic illustrations of three-step synthesis method. The experimental conditions and produced compounds at each step are shown in each box. (C) Out-of-plane x-ray diffraction (XRD) profiles for the direct film and the films at each step. Filled circles indicate reflections coming from the MgAl_2O_4 substrates. Filled and open triangles indicate reflections coming from a sample stage and secondary phases, respectively. arb. units., arbitrary units. (D) XRD ϕ scans of reflections for MgAl_2O_4 440 in the substrate, LiNbO_2 103 in the step 2 film, and $\text{Li}_{1-x}\text{NbO}_2$ 103 in the step 3 film.

(step 3). This solution process is known to take place with the following redox reaction (22)



After the Li^+ ion deintercalation, only small shift of LiNbO_2 00l peaks was observed, suggesting that NbO_2 layers in a host structure were preserved. Note that the crystallinity of the films (full width at half maximum of ω -scan profiles for LiNbO_2 002 reflections) was unchanged.

We also measured asymmetric reflections (Fig. 1D). For both step 2 and step 3 films, the LiNbO_2 103 reflection was clearly observed with a sixfold rotational symmetry, demonstrating solid-phase epitaxy at hexagonal planes (10). The angles of 440 reflections of the substrate coincided with those of the film, indicating an epitaxial relationship of LiNbO_2 [100] || MgAl_2O_4 $\langle 1\bar{1}0 \rangle$. The lattice parameters for step 2 (step 3) films were calculated to be $a = 2.906$ (2.914) Å and $c = 10.446$ (10.468) Å. Bulk values of $\text{Li}_{0.93}\text{NbO}_2$ ($\text{Li}_{0.45}\text{NbO}_2$) were reported to be $a = 2.906$ (2.923) Å and $c = 10.447$ (10.455) Å (16), suggesting that the step 2 films had nearly stoichiometric composi-

tion, while the step 3 films had Li^+ ion deficiency. In addition, the in-plane lattice parameters at each step are considerably larger than that of MgAl_2O_4 ($d_{220} = 2.858$ Å), indicating unstrained film lattices.

Transport properties and strongly correlated electrons

The direct and step 1 films indicated resistivity (ρ) exceeding a measurement limit. Figure 2A shows the temperature dependence of ρ for the films at the following steps. The step 2 films showed ρ less than 10 milliohm-cm at 300 K and metallic conduction ($d\rho/dT > 0$). The step 2 films showed positive Hall coefficient, and hole concentration (n) was estimated to be $2.4 \times 10^{21} \text{ cm}^{-3}$ at 300 K (see section S2). On the other hand, decrease in ρ and change of the film color were found over the course of days, suggesting that oxidation upon exposure to air led to hole doping (23). To avoid any reaction in air, we prepared a capping layer (several-nanometer-thick amorphous alumina) before removing from the chamber (capped step 2). The capped step 2 films showed insulating behavior ($d\rho/dT < 0$) with higher ρ (50 milliohm-cm at 300 K) and lower n ($6.4 \times 10^{20} \text{ cm}^{-3}$ at 300 K). Therefore, it is concluded that the metallic conduction in the step 2 films arises from easily oxidized (hole dopable) nature of LiNbO_2 . It should be emphasized that the electronic ground state of LiNbO_2 has been controversial (17). Our results strongly suggest that LiNbO_2 is an insulator and supports a theoretical study (24).

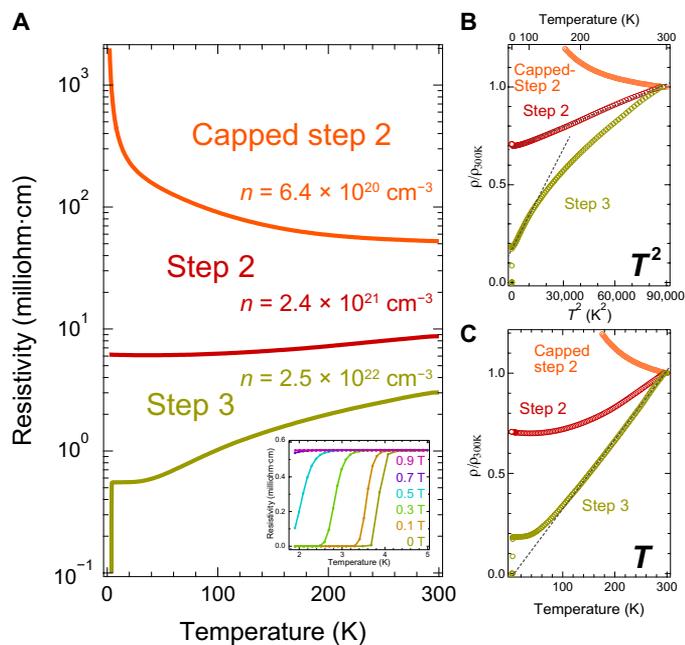


Fig. 2. Transport properties and Fermi-liquid analysis. (A) Temperature dependence of resistivity for the films at each step. The labeled values are hole concentration at 300 K (n) obtained by Hall measurements. Inset: Superconducting properties of the step 3 films. Magnification of that is indicated in the main panel, and its magnetic field (along the c axis) dependence was taken up to 0.9 T. (B) T and (C) T^2 dependence of ρ normalized by the values at 300 K for the films at each step. Dashed lines are linear fits to the plots.

The step 3 films showed much lower ρ (3 milliohm-cm at 300 K), higher n ($2.5 \times 10^{22} \text{ cm}^{-3}$ at 300 K), and a superconductivity below 4.2 K, demonstrating superconducting transition in $\text{Li}_{1-x}\text{NbO}_2$ triggered by hole doping associated with the Li^+ ion deintercalation. Inset of Fig. 2A shows the magnification in the low-temperature range and modulation of superconductivity under magnetic field applied parallel to the c axis of $\text{Li}_{1-x}\text{NbO}_2$. The superconductivity was completely suppressed under a magnetic field as low as 0.9 T, which supports two-dimensional hole superconductivity in the NbO_2 plane (25). The critical magnetic field is much lower for a polycrystal (26). Moreover, superconductivity remained up to 4.2 T, when magnetic field applied perpendicular to the c axis, details of which will be published elsewhere. Further investigation on the two-dimensional hole superconductivity in our ideal samples is important, especially in connection with two-dimensional superconductors such as TMD and high-critical temperature (T_C) cuprate superconductors.

To elucidate how electron correlation works in $\text{Li}_{1-x}\text{NbO}_2$, we replot Fig. 2A for Fig. 2 (B and C), where the normalized resistivity ($\rho/\rho_{300\text{K}}$) is plotted as a function of T (Fig. 2B) and T^2 (Fig. 2C). A comparison between these plots allows us to elucidate a Fermi-liquid picture in the transport properties. We clearly demonstrate enhanced strength of electron correlation and non-Fermi liquid ground states in the superconducting $\text{Li}_{1-x}\text{NbO}_2$ films. We observed the linear T^2 dependence of ρ for the metallic step 2 and step 3 films, indicating Fermi-liquid ground states. However, their temperature ranges are different from one to another. The step 2 films showed good linearity lasting up to 300 K. In contrast, the step 3 films showed deviation from ~ 100 K and, instead, followed T linear dependence. This characteristic temperature, referred to as T^* , is regarded as an important

phase point and/or a boundary in electronic phase diagrams of well-known cuprate, iron-pnictide superconductors, and heavy-fermion compounds (27, 28). We find that, in our $\text{Li}_{1-x}\text{NbO}_2$, T^* showed a monotonic decrease by increasing the hole-doping level similar to well-established quantum critical systems, which we wish to publish elsewhere.

We performed fitting of T^2 plots to Fermi-liquid equation, i.e., $\rho = \rho_0 + AT^2$. We obtained $A = 3.3 \times 10^{-2}$ and 5.4×10^{-2} microhm-cm K^{-2} for step 2 and step 3 films, respectively. The A parameters are directly associated with effective mass of carrier m^* ($A \propto m^{*2}$). Conventional metals and metal-oxide conductors exhibit $A \sim 10^{-6}$ microhm-cm K^{-2} (29). On the other hand, strongly correlated metal oxides in the vicinity of Mott-Hubbard transitions (30) and heavy-fermion systems (29) show A in a range of 10^{-3} to 10 microhm-cm K^{-2} . The values obtained for our $\text{Li}_{1-x}\text{NbO}_2$ films are comparable to or larger than those of the latter, reflecting strong electron correlations. Apart from a class of metal oxides, electron correlations in $\text{Li}_{1-x}\text{NbO}_2$ are comparable to that in superconducting $\text{Cu}_{0.07}\text{TiSe}_2$, an intercalated TMDs (1.1×10^{-2} microhm-cm K^{-2}) (31). Furthermore, the roles of electron correlation in electronic structures of $\text{Li}_{1-x}\text{NbO}_2$ are also expected theoretically (32).

Optical properties and strongly isolated band structure

We have observed marked color changes throughout the three-step synthesis as shown in Fig. 3A. The direct and step 1 films indicated dark color typical of doped TMOs. In contrast, the step 2 films indicated characteristic bloody red, which is consistent with the previous

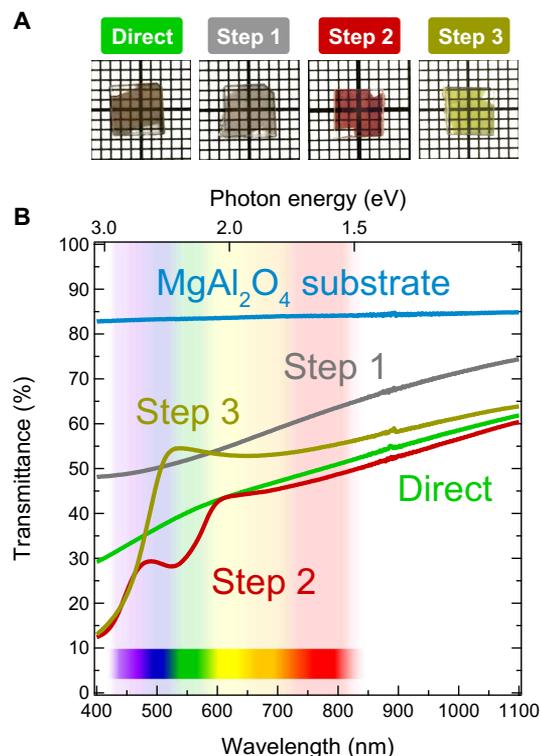


Fig. 3. Sample photographs and optical properties. (A) Optical images of the films at each step. Substrate size is about 5 mm by 5 mm. The transparent regions at the diagonal corners are trace of clamps that were used to hold the substrate to a metal backplate. (B) Optical transmittance spectra for the films at each step and MgAl_2O_4 substrate.

consistent with large A (3.3×10^{-2} and 5.4×10^{-2} microhm-cm K^{-2} for step 2 and step 3 films, respectively) described above. $Li_{1-x}NbO_2$ turned out to form strongly correlated electronic states, resulting in the lower $h\omega_p$ even when n exceeds 10^{22} cm^{-3} . Upon hole doping into $LiNbO_2$, $h\omega_p$ did not shift into the visible range. Thus, further carrier doping is acceptable to enhance the performance of p-TSC.

Regarding (ii), strongly isolated Nb $4d_{z^2}$ band decreased inter-band optical absorption. According to our results and the reported band calculations, the Fermi level (E_F) was thought to locate in the band on Nb $4d_{z^2}$ orbital, which was strongly isolated from the upper (degenerated Nb d_{xy} and $d_{x^2-y^2}$ orbitals) and the lower (O $2p$ orbitals) bands. Note that highly isolated single band has a potential to create high density of states at E_F and strong electron correlation, both of which are favorable to superconductivity (34). The characteristic layered NbO_6 triangular prism structure derives this prominent nature (24) and leads to the anomalous transparency. According to Fig. 5, bandgap becomes wider as E_F drops with increasing n . This effect known as Burstein-Moss effect extends a short wavelength cutoff to blue range (35). Combining these two effects in $Li_{1-x}NbO_2$ realizes appropriate transparent window ranging from 1.0 to 2.4 eV. One expects to expand this window to violet upon further deintercalation of Li^+ ions. Synergetic increase in σ allows $Li_{1-x}NbO_2$ to approach to ITO (Fig. 4). The transmittance can also be improved by reducing film thickness.

In summary, we have first grown two-dimensional $Li_{1-x}NbO_2$ epitaxial films using specialized three-step synthesis method. The hole doping associating the Li^+ ion deintercalation substantially enhances visible-light transparency and leads to superconductivity. We conclude that strongly correlated electrons in the isolated Nb $4d_{z^2}$ band realize the p-type transparent superconductivity in $Li_{1-x}NbO_2$. Our study demonstrates a new approach to creating high-performance TCs.

MATERIALS AND METHODS

Sample fabrication

Li-Nb-O films were grown on $MgAl_2O_4$ (111) substrates using PLD method with KrF excimer laser (1.0 J cm^{-2}). A Li excess ceramic ($Li_{1.2}NbO_{2+\delta}$) was prepared by conventional solid-state reaction steps, starting from mixing Li_2CO_3 and Nb_2O_5 powders with a molar ratio of 1.2:1. The direct growth was conducted at substrate temperature (T_s) of 800°C under a chamber pressure (P_{Ar/H_2}) of 0.1 mtorr set by continuous flow of Ar/H_2 (1 volume percent H_2) gas. The three-step synthesis method is illustrated in Fig. 1B. In step 1, using $Li_{1.2}NbO_{2+\delta}$ target, amorphous Li-Nb-O films were deposited in vacuum (background pressure, 1.0×10^{-7} torr) at RT. In step 2, Ar/H_2 gas was fed into the chamber to set $P_{Ar/H_2} = 0.1$ mtorr, and the step 1 films were annealed in situ at $T_s = 800^\circ\text{C}$ for 1 hour. In step 3, the step 2 films were exposed to air and immersed in 0.02 M I_2/CH_3CN solution for 15 min. Some films were capped by several-nanometer-thick alumina films using PLD at RT in vacuum for avoiding reactions with air (capped step 2).

Characterizations

Using a stylus profiler, film thickness was regulated to be ~ 100 nm. The crystal structures and epitaxial relationship were investigated by a laboratory XRD apparatus with Cu $K\alpha_1$ radiation. The temperature dependence of resistivity and the Hall voltage were measured by a standard four-probe method using a physical property

measurement system (Quantum Design). The optical properties were investigated by ultraviolet-visible near-infrared spectroscopy at RT.

SUPPLEMENTARY MATERIALS

Supplementary material for this article is available at <http://advances.sciencemag.org/cgi/content/full/6/29/eabb8570/DC1>

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